

FEATURES:

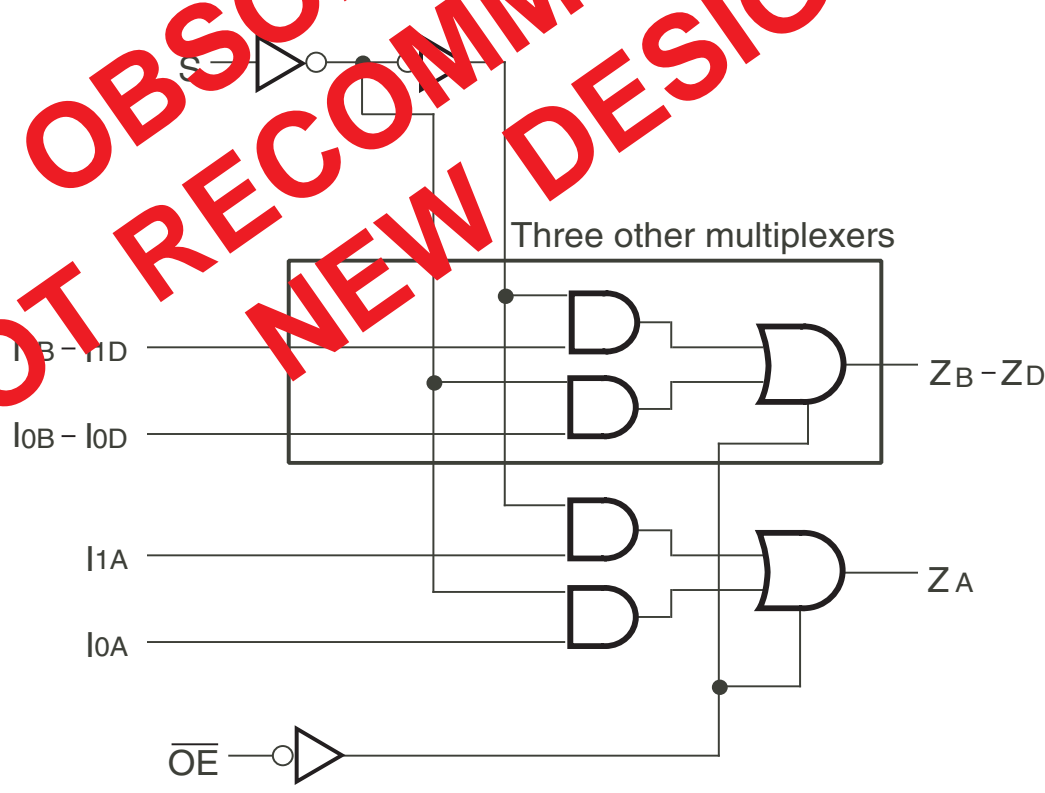
- A, C, and D grades
- Low input and output leakage  $\leq 1\mu\text{A}$  (max.)
- CMOS power levels
- True TTL input and output compatibility:
  - $V_{OH} = 3.3V$  (typ.)
  - $V_{OL} = 0.3V$  (typ.)
- High Drive outputs (-15mA  $I_{OH}$ , 48mA  $I_{OL}$ )
- Meets or exceeds JEDEC standard 18 specifications
- Power off disable outputs permit "live insertion"
- Available in SOIC and QSOP packages

DESCRIPTION:

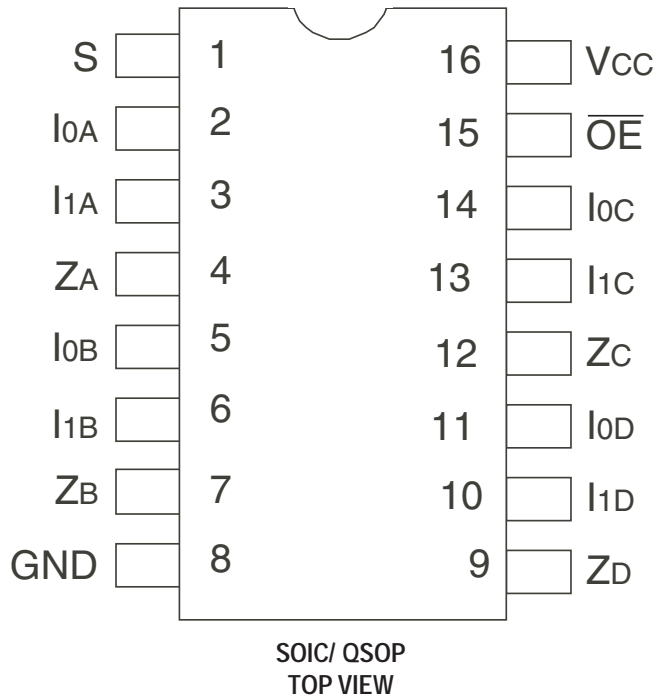
The FCT257T is a high-speed quad 2-input multiplexer built using an advanced dual metal CMOS technology. Four bits of data from two sources can be selected using the common select input. The four buffered outputs present the selected data in the true (non-inverting) form.

The FCT257T has a common Output Enable ( $\overline{OE}$ ) input. When  $\overline{OE}$  is high, all outputs are switched to a high-impedance state, allowing the outputs to interface directly with bus-oriented systems.

FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION



ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>

Symbol	Description	Max	Unit
VTERM <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +7	V
VTERM <sup>(3)</sup>	Terminal Voltage with Respect to GND	-0.5 to Vcc+0.5	V
TSTG	Storage Temperature	-65 to +150	°C
IOUT	DC Output Current	-60 to +120	mA

NOTES:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability. No terminal voltage may exceed Vcc by +0.5V unless otherwise noted.
2. Inputs and Vcc terminals only.
3. Output and I/O terminals only.

CAPACITANCE (TA = +25°C, F = 1.0MHz)

Symbol	Parameter <sup>(1)</sup>	Conditions	Typ.	Max.	Unit
CIN	Input Capacitance	VIN = 0V	6	10	pF
COUT	Output Capacitance	VOU = 0V	8	12	pF

NOTE:

1. This parameter is measured at characterization but not tested.

PIN DESCRIPTION

Pin Names	Description
I0A-I0D	Source 0 Data Inputs
I1A-I1D	Source 1 Data Inputs
OE	Output Enable (Active LOW)
S	Select Input
ZA-ZD	Outputs

FUNCTION TABLE<sup>(1)</sup>

Inputs				Output Zx
OE	S	I0	I1	
H	X	X	X	Z
L	H	X	L	L
L	H	X	H	H
L	L	L	X	L
L	L	H	X	H

NOTE:

1. H = HIGH Voltage Level  
L = LOW Voltage Level  
X = Don't Care  
Z = High-Impedance

## DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Industrial:  $T_A = -40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$ ,  $V_{CC} = 5.0\text{V} \pm 5\%$

Symbol	Parameter	Test Conditions <sup>(1)</sup>		Min.	Typ. <sup>(2)</sup>	Max.	Unit
$V_{IH}$	Input HIGH Level	Guaranteed Logic HIGH Level		2	—	—	V
$V_{IL}$	Input LOW Level	Guaranteed Logic LOW Level		—	—	0.8	V
$I_{IH}$	Input HIGH Current <sup>(4)</sup>	$V_{CC} = \text{Max.}$	$V_I = 2.7\text{V}$	—	—	$\pm 1$	$\mu\text{A}$
$I_{IL}$	Input LOW Current <sup>(4)</sup>	$V_{CC} = \text{Max.}$	$V_I = 0.5\text{V}$	—	—	$\pm 1$	$\mu\text{A}$
$I_{OZH}$	High Impedance Output Current (3-State output pins) <sup>(4)</sup>	$V_{CC} = \text{Max.}$	$V_O = 2.7\text{V}$	—	—	$\pm 1$	$\mu\text{A}$
$I_{OZL}$			$V_O = 0.5\text{V}$	—	—	$\pm 1$	
$I_I$	Input HIGH Current <sup>(4)</sup>	$V_{CC} = \text{Max.}, V_I = V_{CC} (\text{Max.})$		—	—	$\pm 1$	$\mu\text{A}$
$V_{IK}$	Clamp Diode Voltage	$V_{CC} = \text{Min.}, I_{IN} = -18\text{mA}$		—	-0.7	-1.2	V
$V_H$	Input Hysteresis	—		—	200	—	mV
$I_{CC}$	Quiescent Power Supply Current	$V_{CC} = \text{Max.}, V_{IN} = \text{GND or } V_{CC}$		—	0.01	1	mA

## OUTPUT DRIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions <sup>(1)</sup>		Min.	Typ. <sup>(2)</sup>	Max.	Unit
$V_{OH}$	Output HIGH Voltage	$V_{CC} = \text{Min.}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -8\text{mA}$	2.4	3.3	—	V
			$I_{OH} = -15\text{mA}$	2	3	—	
$V_{OL}$	Output LOW Voltage	$V_{CC} = \text{Min.}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 48\text{mA}$	—	0.3	0.5	V
$I_{OS}$	Short Circuit Current	$V_{CC} = \text{Max.}, V_O = \text{GND}^{(3)}$		-60	-120	-225	mA
$I_{OFF}$	Input/Output Power Off Leakage <sup>(5)</sup>	$V_{CC} = 0\text{V}, V_{IN} \text{ or } V_O \leq 4.5\text{V}$		—	—	$\pm 1$	$\mu\text{A}$

### NOTES:

1. For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.
2. Typical values are at  $V_{CC} = 5.0\text{V}$ ,  $+25^{\circ}\text{C}$  ambient.
3. Not more than one output should be tested at one time. Duration of the test should not exceed one second.
4. The test limit for this parameter is  $\pm 5\mu\text{A}$  at  $T_A = -55^{\circ}\text{C}$ .
5. This parameter is guaranteed but not tested.

## POWER SUPPLY CHARACTERISTICS

Symbol	Parameter	Test Conditions <sup>(1)</sup>		Min.	Typ. <sup>(2)</sup>	Max.	Unit
$\Delta I_{CC}$	Quiescent Power Supply Current TTL Inputs HIGH	$V_{CC} = \text{Max.}$ $V_{IN} = 3.4V^{(3)}$		—	0.5	2	mA
$I_{CCD}$	Dynamic Power Supply Current <sup>(4)</sup>	$V_{CC} = \text{Max.}$ Outputs Open $\overline{OE} = \text{GND}$ One Input Toggling 50% Duty Cycle	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	0.15	0.25	mA/ MHz
$I_C$	Total Power Supply Current <sup>(6)</sup>	$V_{CC} = \text{Max.}$ Outputs Open $f_o = 10\text{MHz}$ 50% Duty Cycle $\overline{OE} = \text{GND}$ One Bit Toggling	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	1.5	3.5	mA
			$V_{IN} = 3.4V$ $V_{IN} = \text{GND}$	—	1.8	4.5	
		$V_{CC} = \text{Max.}$ Outputs Open $f_o = 2.5\text{MHz}$ 50% Duty Cycle $\overline{OE} = \text{GND}$ Four Bits Toggling	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	1.5	3.5 <sup>(5)</sup>	
			$V_{IN} = 3.4V$ $V_{IN} = \text{GND}$	—	2.5	7.5 <sup>(5)</sup>	

**NOTES:**

- For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.
  - Typical values are at  $V_{CC} = 5.0V$ ,  $+25^\circ\text{C}$  ambient.
  - Per TTL driven input; ( $V_{IN} = 3.4V$ ). All other inputs at  $V_{CC}$  or  $\text{GND}$ .
  - This parameter is not directly testable, but is derived for use in Total Power Supply Calculations.
  - Values for these conditions are examples of  $\Delta I_{CC}$  formula. These limits are guaranteed but not tested.
  - $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$   
 $I_C = I_{CC} + \Delta I_{CC} \text{DH}Nt + I_{CCD} (foNo)$   
 $I_{CC} = \text{Quiescent Current}$   
 $\Delta I_{CC} = \text{Power Supply Current for a TTL High Input } (V_{IN} = 3.4V)$   
 $\text{DH} = \text{Duty Cycle for TTL Inputs High}$   
 $Nt = \text{Number of TTL Inputs at DH}$   
 $I_{CCD} = \text{Dynamic Current caused by an Input Transition Pair (HLH or LHL)}$   
 $f_o = \text{Output Frequency}$   
 $No = \text{Number of Outputs at } f_o$
- All currents are in milliamps and all frequencies are in megahertz.

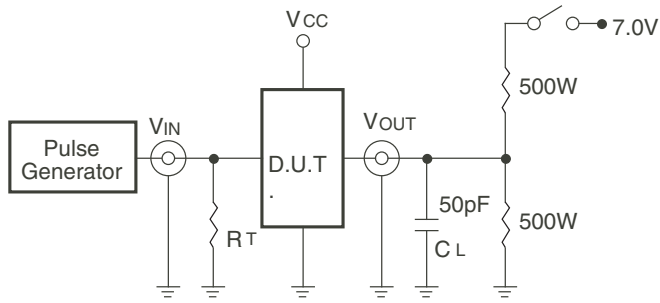
## SWITCHING CHARACTERISTICS OVER OPERATING RANGE

Symbol	Parameter	Condition <sup>(1)</sup>	FCT257AT		FCT275CT		FCT275DT		Unit
			Min. <sup>(2)</sup>	Max.	Min. <sup>(2)</sup>	Max.	Min. <sup>(2)</sup>	Max.	
$t_{PLH}$ $t_{PHL}$	Propagation Delay Ix to Zx	$C_L = 50\text{pF}$ $R_L = 500\Omega$	1.5	5	1.5	4.3	1.5	3.9	ns
$t_{PLH}$ $t_{PHL}$	Propagation Delay S to Zx		1.5	7	1.5	5.2	1.5	4.4	ns
$t_{PZH}$ $t_{PZL}$	Output Enable Time		1.5	7	1.5	6	1.5	4.4	ns
$t_{PHZ}$ $t_{PLZ}$	Output Disable Time		1.5	5.5	1.5	5	1.5	4.4	ns

**NOTES:**

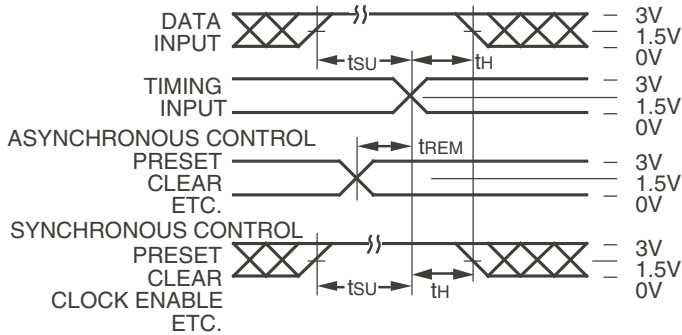
- See test circuit and waveforms.
- Minimum limits are guaranteed but not tested on Propagation Delays.

TEST CIRCUITS AND WAVEFORMS



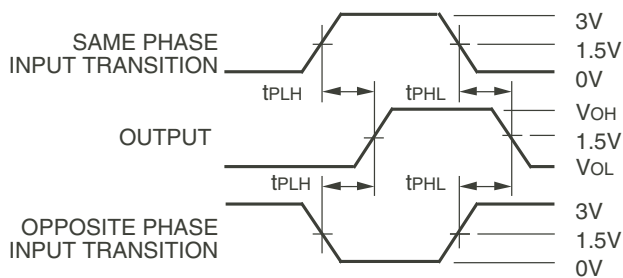
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Test Circuits for All Outputs



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Set-Up, Hold, and Release Times



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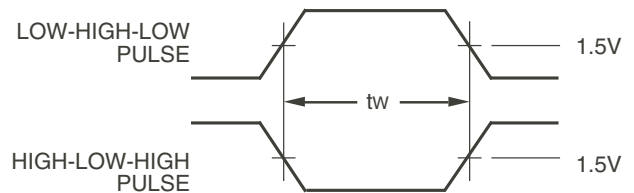
Propagation Delay

SWITCH POSITION

Test	Switch
Open Drain Disable Low Enable Low	Closed
All Other Tests	Open

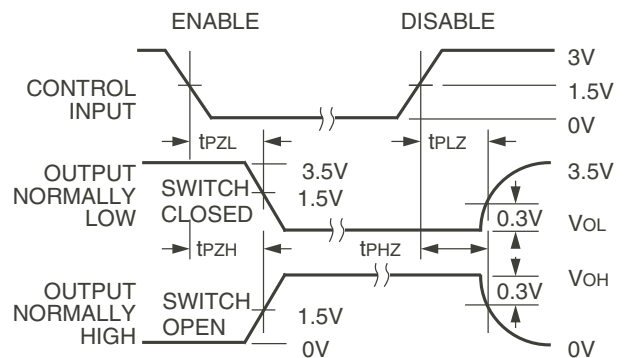
DEFINITIONS:

CL = Load capacitance: includes jig and probe capacitance.  
RT = Termination resistance: should be equal to ZOUT of the Pulse Generator.



Pulse Width

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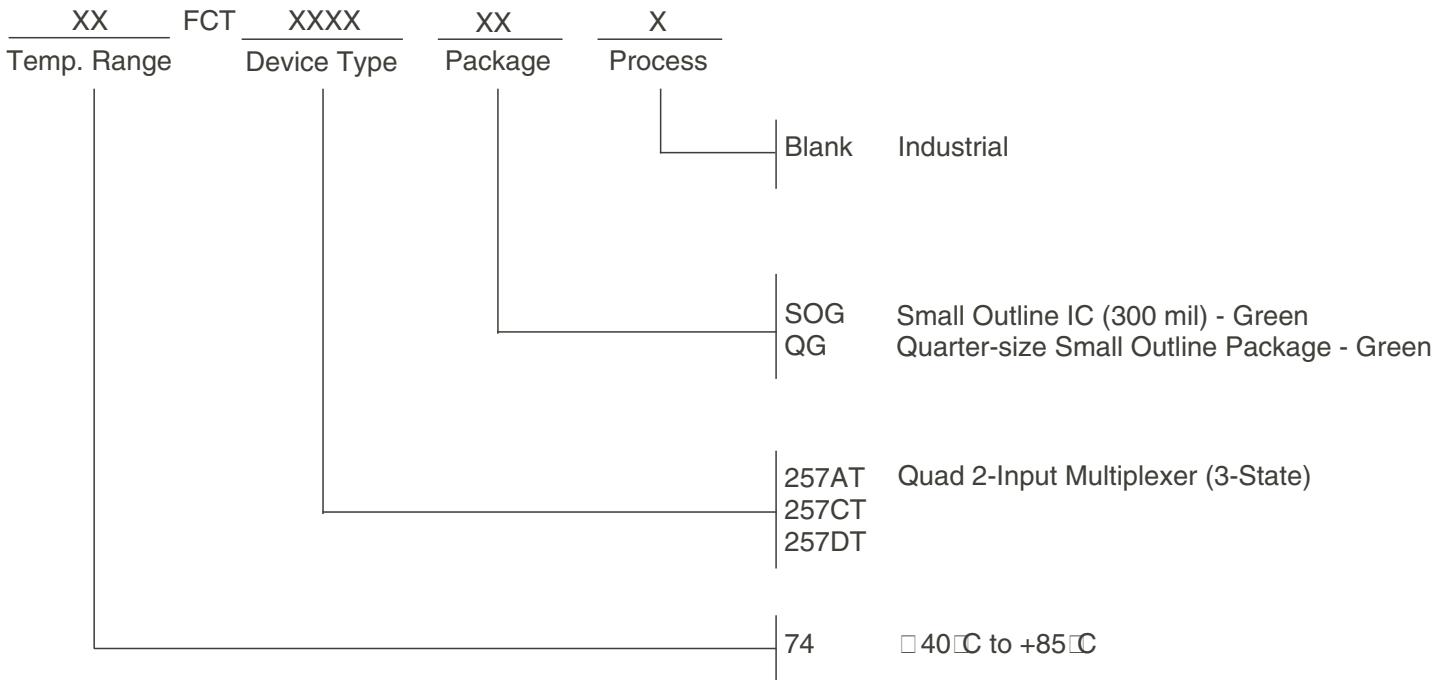
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Enable and Disable Times

NOTES:

1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.
2. Pulse Generator for All Pulses: Rate ≤ 1.0MHz; tr ≤ 2.5ns; tr ≤ 2.5ns.

ORDERING INFORMATION



Datasheet Document History

<p>09/29/2009 08/14/2015 09/03/2019</p>	<p>Pg. 6 Updated the ordering information by removing the "IDT" notation and non RoHS part. PDN# CQ-15-04 issued. See IDT.com for PDN specifics. Datasheet changed to Obsolete Status.</p>
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